

#### < C band internally matched power GaAs FET >

## **MGFC39V3742A**

3.7 - 4.2 GHz BAND / 8W

#### **DESCRIPTION**

The MGFC39V3742A is an internally impedance-matched GaAs power FET especially designed for use in 3.7 – 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

#### **FEATURES**

Class A operation

Internally matched to 50(ohm) system

- High output power
  - P1dB=8W (TYP.) @f=3.7 4.2GHz
- High power gain
  - GLP=12.0dB (TYP.) @f=3.7 4.2GHz
- High power added efficiency
  - P.A.E.=31% (TYP.) @f=3.7 4.2GHz
- Low distortion [item -51]
  - IM3=-45dBc (TYP.) @Po=28dBm S.C.L

#### **APPLICATION**

- item 01: 3.7 4.2 GHz band power amplifier
- item 51: 3.7 4.2 GHz band digital radio communication

#### **QUALITY**

• IG

#### RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A • RG=50ohm Refer to Bias Procedure

#### **Absolute maximum ratings** (Ta=25°C)

V
V
Α
mA
mA
W
°C
°C
_

1 : Tc=25°C

# OUTLINE DRAWING Unit: millimeters 21.0 +/-0.3 12.9 +/-0.2 (3)

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#### Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	7.5	Α
gm	Transconductance	VDS=3V,ID=2.2A	-	2	i	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	38	39.5	i	dBm
GLP	Linear Power Gain	f=3.7 – 4.2GHz	9	12	-	dB
ID	Drain current		-	-	3	Α
P.A.E.	Power added efficiency		-	31	-	%
IM3 *2	3rd order IM distortion		-42	-45	=	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	=	3.5	°C/W

<sup>\*2 :</sup>item -51 ,2 tone test,Po=28dBm Single Carrier Level ,f=4.2GHz,delta f=10MHz

<sup>\*3:</sup> Channel-case

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